

LPDDR5X SDRAM

**MT62F1G16D1, MT62F1G32D2, MT62F2G32D4, MT62F4G32D8,
MT62F1G64D4, MT62F2G64D8**

Features

- **Architecture**
 - 17.1 GB/s maximum bandwidth per channel
 - Frequency range: 1067–5 MHz (data rate range per pin: 8533–40 Mb/s with WCK:CK = 4:1)
 - Selectable CKR (WCK:CK = 2:1 or 4:1)
- **LPDDR5X/LPDDR5 data interface**
 - Single x16 channel/die
 - Double-data-rate command/address entry
 - Differential command clocks (CK_t/CK_c) for high-speed operation
 - Differential data clocks (WCK_t/WCK_c)
 - Optional differential read strobe (RDQS_t/RDQS_c)
 - 16n-bit or 32n-bit prefetch architecture
 - Bank Architecture: 8-bank (8B) mode, bank group (BG) mode, and 16-bank (16B) mode supported
 - Command-selectable burst lengths (BL = 16 or 32) in bank group or 16-bank modes
 - Background ZQ calibration/command-based ZQ calibration
 - Optional link protection (link ECC)
 - Partial-array self refresh (PASR) and partial-array auto refresh (PAAR) with segment mask
- **Ultra-low-voltage core and I/O power supplies**
 - V_{DD1} = 1.70–1.95V; 1.80V TYP
 - V_{DD2H} = 1.01–1.12V; 1.05V TYP
 - V_{DD2L} = V_{DD2H} or 0.87–0.97V; 0.90V TYP
 - V_{DDQ} = 0.50V or 0.45V¹ TYP; 0.30V TYP (ODT off only)
- **I/O characteristics**
 - Interface-LVSTL 0.5/0.3
 - I/O type: Low-swing single-ended, V_{SS} terminated
 - V_{OH}-compensated output drive
 - Programmable V_{SS} on-die termination (ODT)
 - Non target ODT support
 - DVFSQ support
- **Low power features**
 - DVFSC: Dynamic voltage frequency scaling core
 - Single-ended CK, single-ended WCK and single-ended RDQS
 - Data copy
 - Write X

Options

- **Operating Voltage**
 - V_{DD1}/V_{DD2H}/V_{DD2L}/V_{DDQ}/V_{DDQ} (ODT off only): 1.80V/1.05V/V_{DD2H} or 0.90V/0.50V or 0.45V¹/0.30V
- **Array Configuration**

– 1 Gig x 16 (1Gx16 x 1 Ch x 1R)	1G16
– 1 Gig x 32 (1Gx16 x 2 Ch x 1R)	1G32
– 2 Gig x 32 (1Gx16 x 2 Ch x 2R)	2G32
– 4 Gig x 32 (2Gx8 x 2 Ch x 2R)	4G32
– 1Gig x 64 (1Gx16 x 4 Ch x 1R)	1G64
– 2 Gig x 64 (1Gx16 x 4 Ch x 2R)	2G64
- **Device configuration**

– 1 die in package (1G16 x 1 die)	D1
– 2 die in package (1G16 x 2 die)	D2
– 4 die in package (1G16 x 4 die)	D4
– 8 die in package (2G8 x 8 die)	D8
– 8 die in package (1G16 x 8 die)	D8
- **FBGA RoHS-compliant “green” package**

– 315-ball TFBGA 12.4mm x 15.0mm (TYP), seated height 1.1mm (MAX)	DS
– 315-ball LFBGA 12.4mm x 15.0mm (TYP), seated height 1.3mm (MAX)	DV
– 441-ball TFBGA 14.0mm x 14.0mm (TYP), seated height 1.1mm (MAX)	EK
- **Speed grade, cycle time (^tWCK)**

– 8533 Mb/s	-023
– 7500 Mb/s	-026
- **Operating Temperature:**

– –25°C ≤ T _C ≤ +85°C	WT
– –40°C ≤ T _C ≤ +95°C	IT
- **Revision**

	:B
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Note: 1. V_{DDQ} = 0.45V (TYP) only supported in 441-ball package up to 6400 Mb/s.



Part Number Ordering Information

Figure 1: Part Number Chart

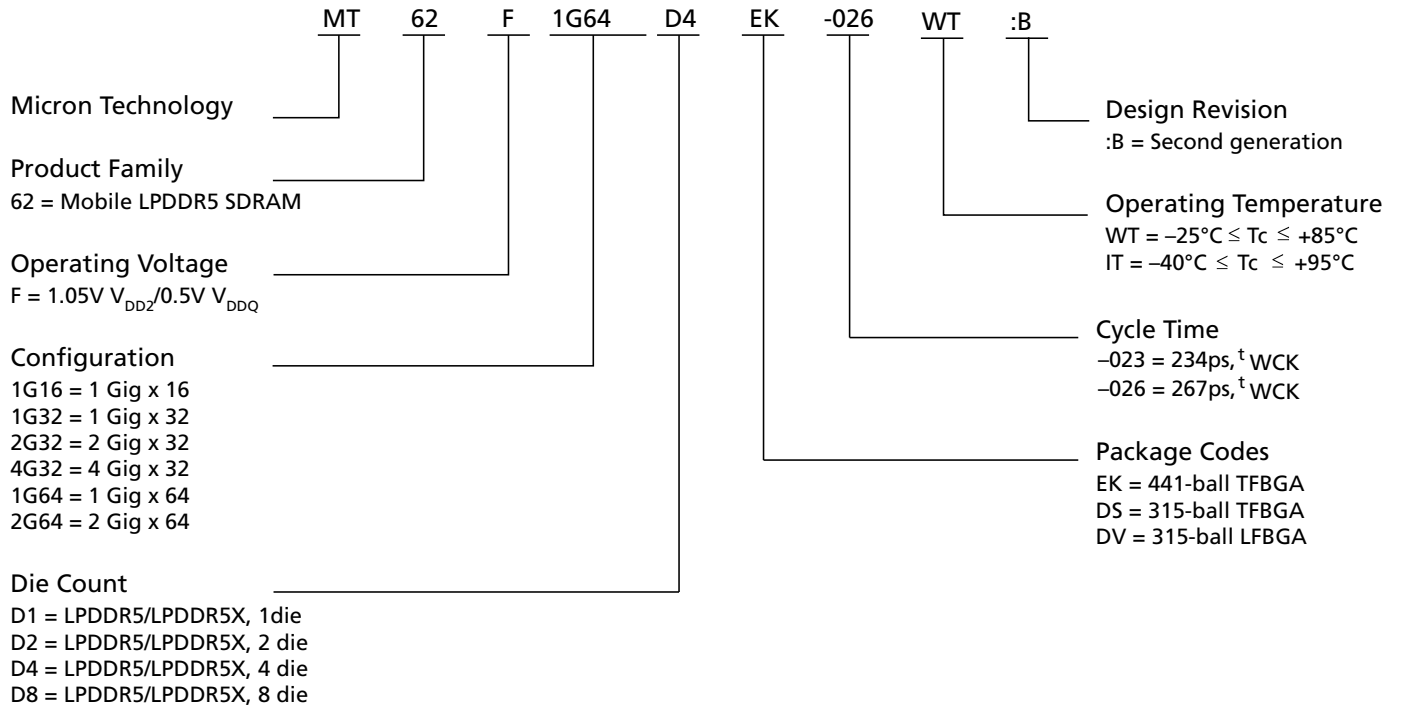


Table 1: Part Number List

Part Number	Total Density	Data Rate per Pin
MT62F1G16D1DS-023 IT:B	2GB (16Gb)	8533 Mb/s
MT62F1G32D2DS-023 IT:B	4GB (32Gb)	
MT62F1G32D2DS-023 WT:B		
MT62F2G32D4DS-023 IT:B	8GB (64Gb)	
MT62F2G32D4DS-023 WT:B		7500 Mb/s
MT62F4G32D8DV-023 IT:B	16GB (128Gb)	
MT62F4G32D8DV-023 WT:B		
MT62F1G64D4EK-023 WT:B	8GB (64Gb)	
MT62F2G64D8EK-023 WT:B	16GB (128Gb)	7500 Mb/s
MT62F1G32D2DS-026 WT:B	4GB (32Gb)	
MT62F2G32D4DS-026 WT:B	8GB (64Gb)	
MT62F4G32D8DV-026 WT:B	16GB (128Gb)	
MT62F1G64D4EK-026 WT:B	8GB (64Gb)	
MT62F2G64D8EK-026 WT:B	16GB (128Gb)	



FBGA Part Marking Decoder

Due to space limitations, FBGA-packaged components have an abbreviated part marking that is different from the part number. Micron's FBGA part marking decoder is available at www.micron.com/decoder.

LPDDR5/LPDDR5X Data Sheet List

For general LPDDR5/LPDDR5X specifications, please refer to the data sheets below.

- General LPDDR5/LPDDR5X Specifications 1: Mode Registers
- General LPDDR5/LPDDR5X Specifications 2: AC/DC and Interface Specifications
- General LPDDR5/LPDDR5X Specifications 3: Features and Functionalities

Contents

Part Number Ordering Information	2
FBGA Part Marking Decoder	3
LPDDR5/LPDDR5X Data Sheet List	3
Important Notes and Warnings	7
General Notes	8
Device Configuration	9
Refresh Requirement Parameters	11
Package Block Diagrams	12
Single Die, Single Channel, Single Rank	12
Dual Die, Dual Channel, Single Rank	12
Quad Die, Dual Channel, Dual Rank	13
Eight Die, Dual Channel, Dual Rank	14
Quad Die, Quad Channel, Single Rank	15
Eight Die, Quad Channel, Dual Rank	16
Ball Assignments and Descriptions	17
315b Single Die, Single Channel, 1 Rank	17
315b Dual Channel, 1 Rank, 2 Rank	19
441b Quad Channel, 1 Rank, 2 Rank	21
Package Dimensions	23
315-Ball Package (Package Code: DS)	23
315-Ball Package (Package Code: DV)	24
441-Ball Package (Package Code: EK)	25
Product-Specific Mode Register Definition	26
I _{DD} Parameters	28
Revision History	34
Rev. D – 11/2022	34
Rev. C – 06/2022	34
Rev. B – 04/2022	34
Rev. A – 02/2022	34

List of Figures

Figure 1: Part Number Chart	2
Figure 2: Single-Die, Single-Channel, Single-Rank Package Block Diagram	12
Figure 3: Dual-Die, Dual-Channel, Single-Rank Package Block Diagram	12
Figure 4: Quad-Die, Dual-Channel, Dual-Rank Package Block Diagram	13
Figure 5: Eight-Die, Dual-Channel, Dual-Rank Package Block Diagram	14
Figure 6: Quad-Die, Quad-Channel, Single-Rank Package Block Diagram	15
Figure 7: Eight-Die, Quad-Channel, Dual-Rank Package Block Diagram	16
Figure 8: 315-Ball Single-Channel Discrete FBGA	18
Figure 9: 315-Ball Dual-Channel Discrete FBGA	20
Figure 10: 441-Ball Quad-Channel FBGA	22
Figure 11: 315-Ball TFBGA – 12.4mm (TYP) × 15.0mm (TYP) × 1.1mm (MAX) (Package Code: DS)	23
Figure 12: 315-Ball LFBGA – 12.4mm (TYP) × 15.0mm (TYP) × 1.3mm (MAX) (Package Code: DV)	24
Figure 13: 441-Ball TFBGA – 14.0mm (TYP) × 14.0mm (TYP) × 1.1mm (MAX) (Package Code: EK)	25

List of Tables

Table 1: Part Number List	2
Table 2: Die Organization in the Package (x16)	9
Table 3: Die Organization in the Package (x32)	9
Table 4: Die Organization in the Package (x64)	10
Table 5: Die Addressing	10
Table 6: Refresh Requirement Parameters	11
Table 7: Single Channel 315-Ball/Pad Descriptions	17
Table 8: 315-Ball/Pad Descriptions	19
Table 9: 441-Ball/Pad Descriptions	21
Table 10: Mode Register Contents	26
Table 11: WT I _{DD} Parameters – Single Die	28
Table 12: WT Full-Array Power-Down Self Refresh Current – Single Die	30
Table 13: IT I _{DD} Parameters – Single Die	31
Table 14: IT Full-Array Power-Down Self Refresh Current – Single Die	33

Important Notes and Warnings

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General Notes

Throughout the data sheet, figures and text refer to DQs as DQ. DQ should be interpreted as any or all DQs collectively, unless specifically stated otherwise.

RDQS, CK, and WCK should be interpreted as RDQS_t, RDQS_c, CK_t, CK_c, and WCK_t, WCK_c respectively unless specifically stated otherwise. CA includes all CA pins used for a given density.

In timing diagrams, CMD is used as an indicator only. Actual signals occur on CA[6:0].

V_{REF} indicates $V_{REF(CA)}$ and $V_{REF(DQ)}$.

Complete functionality is described throughout the entire document. Any page or diagram may have been simplified to convey a topic and may not be inclusive of all requirements.

Any specific requirement takes precedence over a general statement.

Any functionality not specifically stated herein is considered undefined, illegal, is not supported, and will result in unknown operation.



Device Configuration

Table 2: Die Organization in the Package (x16)

Die Organization	1G16 (16 Gb/package)
Channel A	x16 mode × 1 die

Note: 1. Refer to the Package Block Diagram section in this data sheet.

Table 3: Die Organization in the Package (x32)

Die Organization	1G32 (32 Gb/package)	2G32 (64 Gb/package)	4G32 (128 Gb/package)
Channel A	x16 mode × 1 die	–	–
Channel B	x16 mode × 1 die	–	–
Channel A, rank 0	–	x16 mode × 1 die	–
Channel B, rank 0	–	x16 mode × 1 die	–
Channel A, rank 1	–	x16 mode × 1 die	–
Channel B, rank 1	–	x16 mode × 1 die	–
Channel A, rank 0 DQ[7:0]	–	–	x8 mode × 1 die
Channel A, rank 1 DQ[7:0]	–	–	x8 mode × 1 die
Channel B, rank 0 DQ[7:0]	–	–	x8 mode × 1 die
Channel B, rank 1 DQ[7:0]	–	–	x8 mode × 1 die
Channel A, rank 0 DQ[15:8]	–	–	x8 mode × 1 die
Channel A, rank 1 DQ[15:8]	–	–	x8 mode × 1 die
Channel B, rank 0 DQ[15:8]	–	–	x8 mode × 1 die
Channel B, rank 1 DQ[15:8]	–	–	x8 mode × 1 die

Note: 1. Refer to the Package Block Diagram section in this data sheet.



Table 4: Die Organization in the Package (x64)

Die Organization	1G64 (64 Gb/package)	2G64 (128 Gb/package)
Channel A, rank 0	x16 mode × 1 die	x16 mode × 1 die
Channel B, rank 0	x16 mode × 1 die	x16 mode × 1 die
Channel C, rank 0	x16 mode × 1 die	x16 mode × 1 die
Channel D, rank 0	x16 mode × 1 die	x16 mode × 1 die
Channel A, rank 1	–	x16 mode × 1 die
Channel B, rank 1	–	x16 mode × 1 die
Channel C, rank 1	–	x16 mode × 1 die
Channel D, rank 1	–	x16 mode × 1 die

Note: 1. Refer to the Package Block Diagram section in this data sheet.

Table 5: Die Addressing

Description	1G16 (16Gb/package), 1G32 (32 Gb/package), 2G32 (64 Gb/package), 1G64 (64 Gb/package), 2G64 (128 Gb/package)			4G32 (128Gb/package)		
	BG mode	16B mode	8B mode	BG mode	16B mode	8B mode
Density per die	16Gb			16Gb		
Bits	17,179,869,184			17,179,869,184		
Configuration	64Mb × 16 DQ × 4 Banks × 4BG	64Mb × 16 DQ × 16 Banks	128Mb × 16 DQ × 8 Banks	128Mb × 8 DQ × 4 Banks × 4BG	128Mb × 8 DQ × 16 Banks	256Mb × 8 DQ × 8 Banks
Number of banks	4	16	8	4	16	8
Number of bank groups	4	1	1	4	1	1
Array prefetch bits	256	256	512	128	128	256
Rows per bank	65,536			131,072		
Columns	64			64		
Page size (bytes)	2048	2048	4096	1024	1024	2048
Native burst length	16	16	32	16	16	32
Number of I/Os	16			8		
Bank address	BA[1:0]	BA[3:0]	BA[2:0]	BA[1:0]	BA[3:0]	BA[2:0]
Bank group address	BG[1:0]	–	–	BG[1:0]	–	–
Row address	R[15:0]			R[16:0]		
Column address	C[5:0]			C[5:0]		
Burst address	B[3:0]	B[3:0]	B[4:0]	B[3:0]	B[3:0]	B[4:0]
Burst starting address boundary	128-bit			128-bit		

Note: 1. Refer to the SDRAM Addressing section in General LPDDR5/LPDDR5X Specifications 3.



Refresh Requirement Parameters

Table 6: Refresh Requirement Parameters

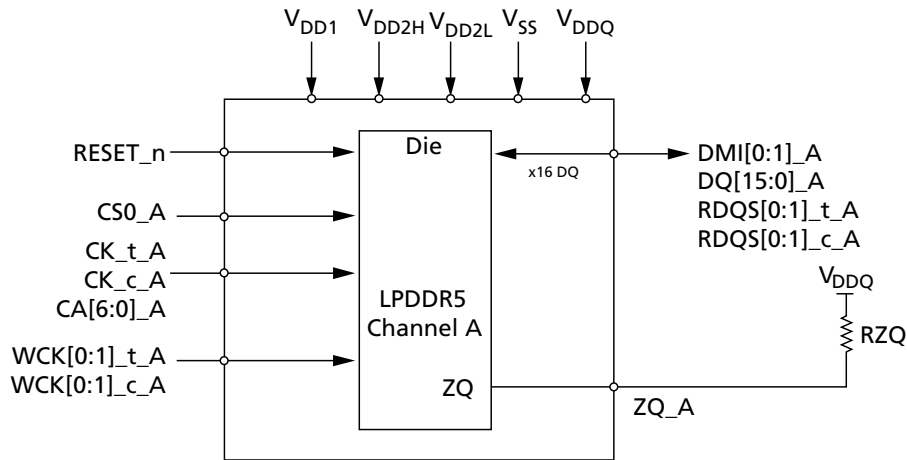
Parameter	Symbol	16Gb Die		Unit
		BG and 16B Mode	8B Mode	
REFRESH cycle time (all banks)	t_{RFCab}	280	280	ns
REFRESH cycle time (per bank)	t_{RFCpb}	140	140	ns
Per bank refresh to per bank refresh time (different bank)	$t_{PBR2PBR}$	90	90	ns
Per bank refresh to ACTIVATE command time (different bank)	$t_{PBR2ACT}$	7.5	10	ns

Note: 1. This table only describes refresh parameters that are density dependent. Refer to Refresh Requirement section in General LPDDR5/LPDDR5X Specifications 3 for all refresh parameters.

Package Block Diagrams

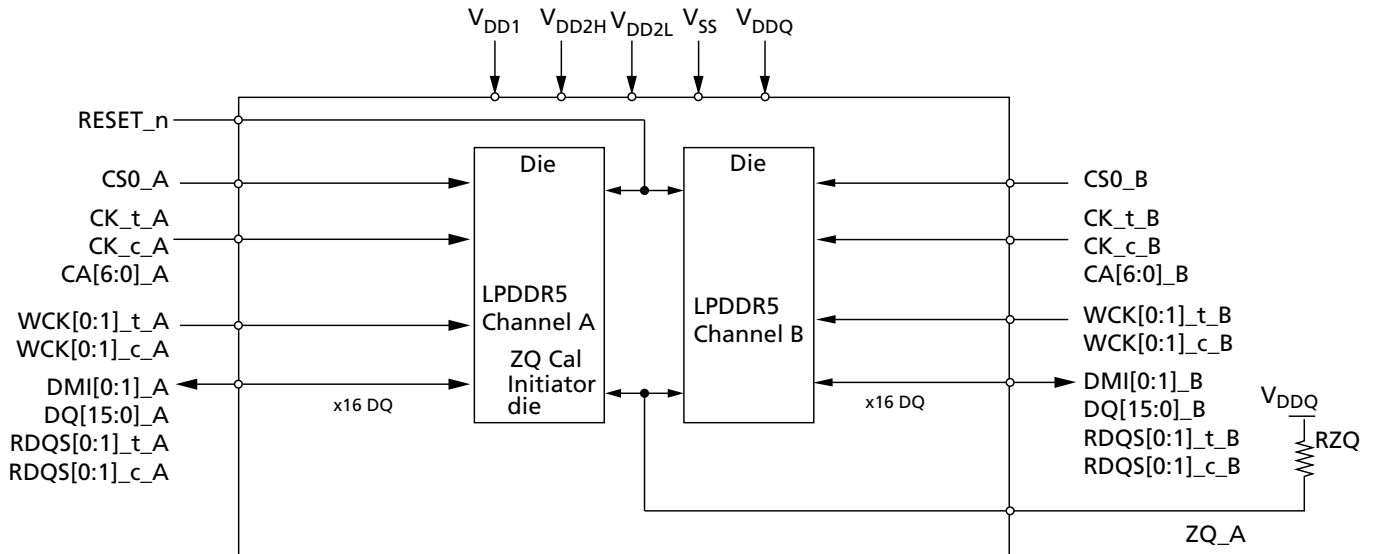
Single Die, Single Channel, Single Rank

Figure 2: Single-Die, Single-Channel, Single-Rank Package Block Diagram



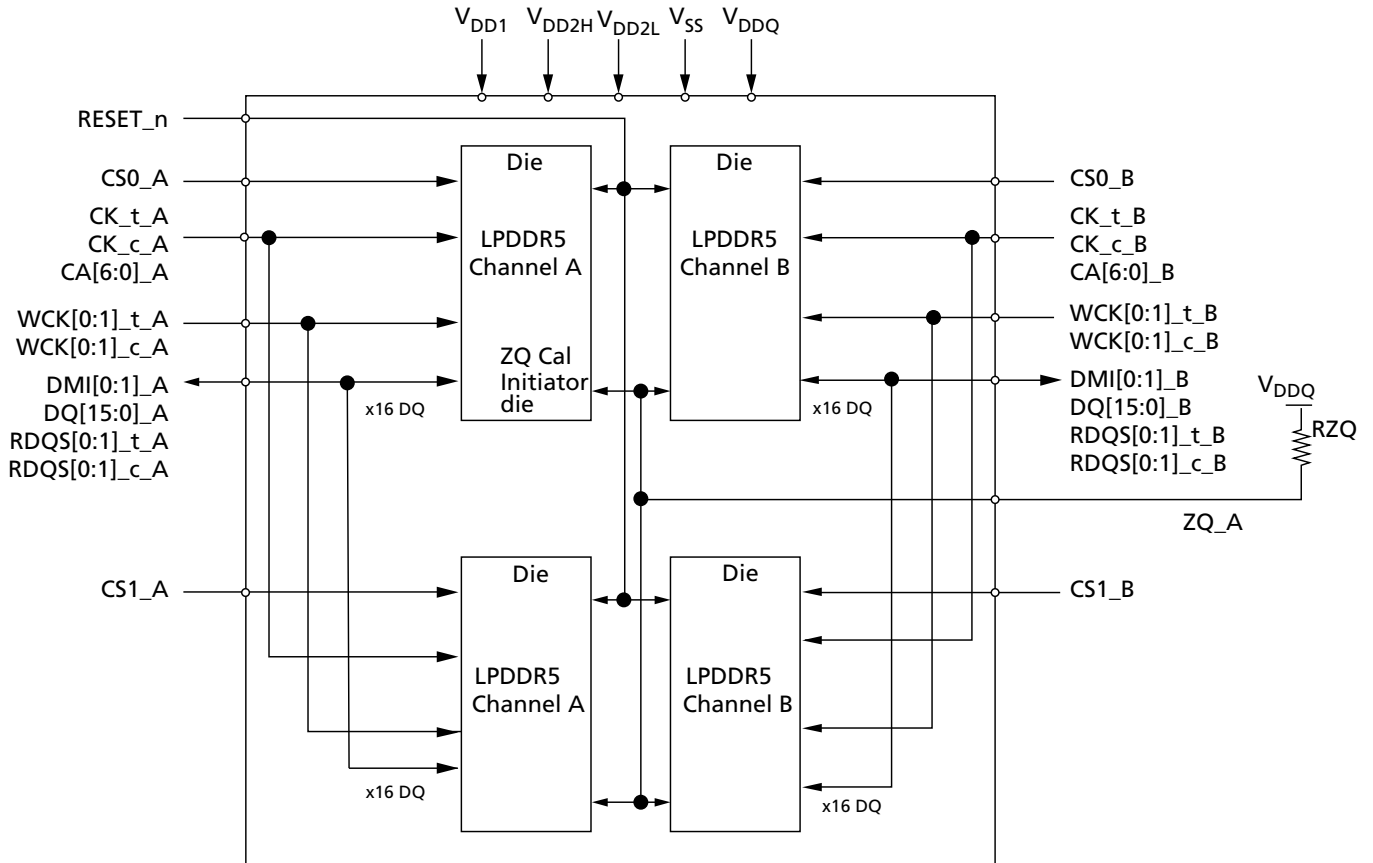
Dual Die, Dual Channel, Single Rank

Figure 3: Dual-Die, Dual-Channel, Single-Rank Package Block Diagram



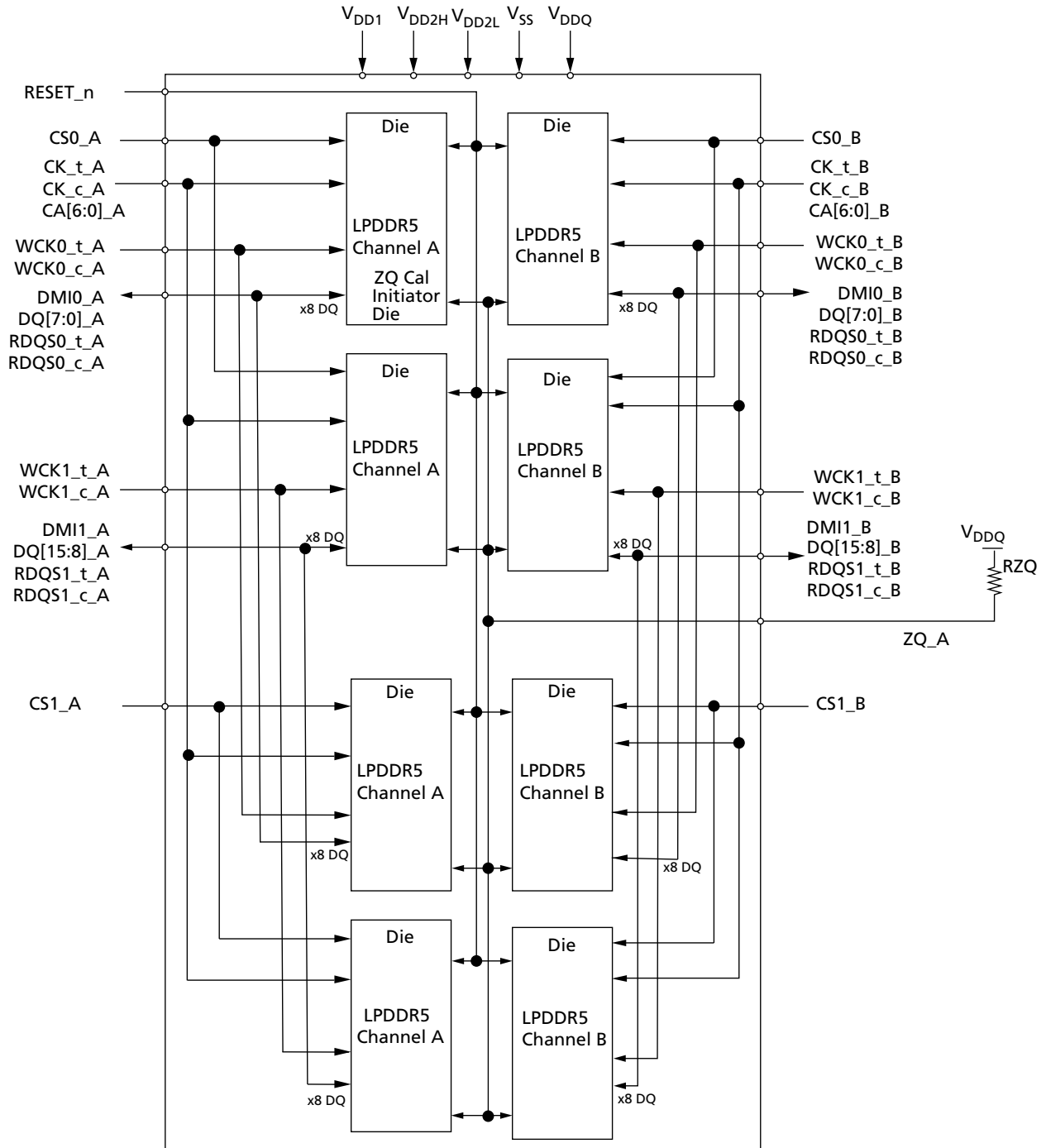
Quad Die, Dual Channel, Dual Rank

Figure 4: Quad-Die, Dual-Channel, Dual-Rank Package Block Diagram



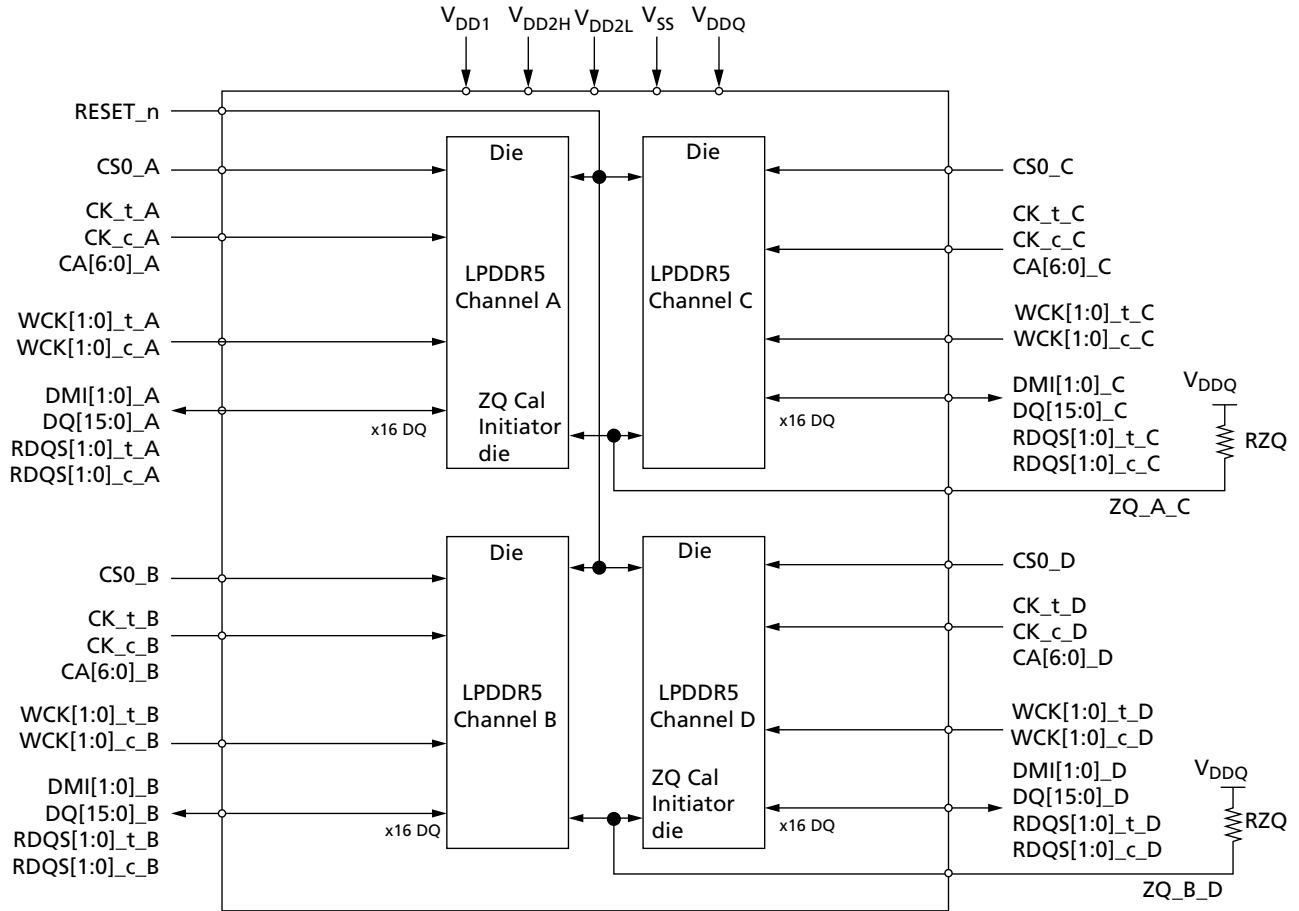
Eight Die, Dual Channel, Dual Rank

Figure 5: Eight-Die, Dual-Channel, Dual-Rank Package Block Diagram



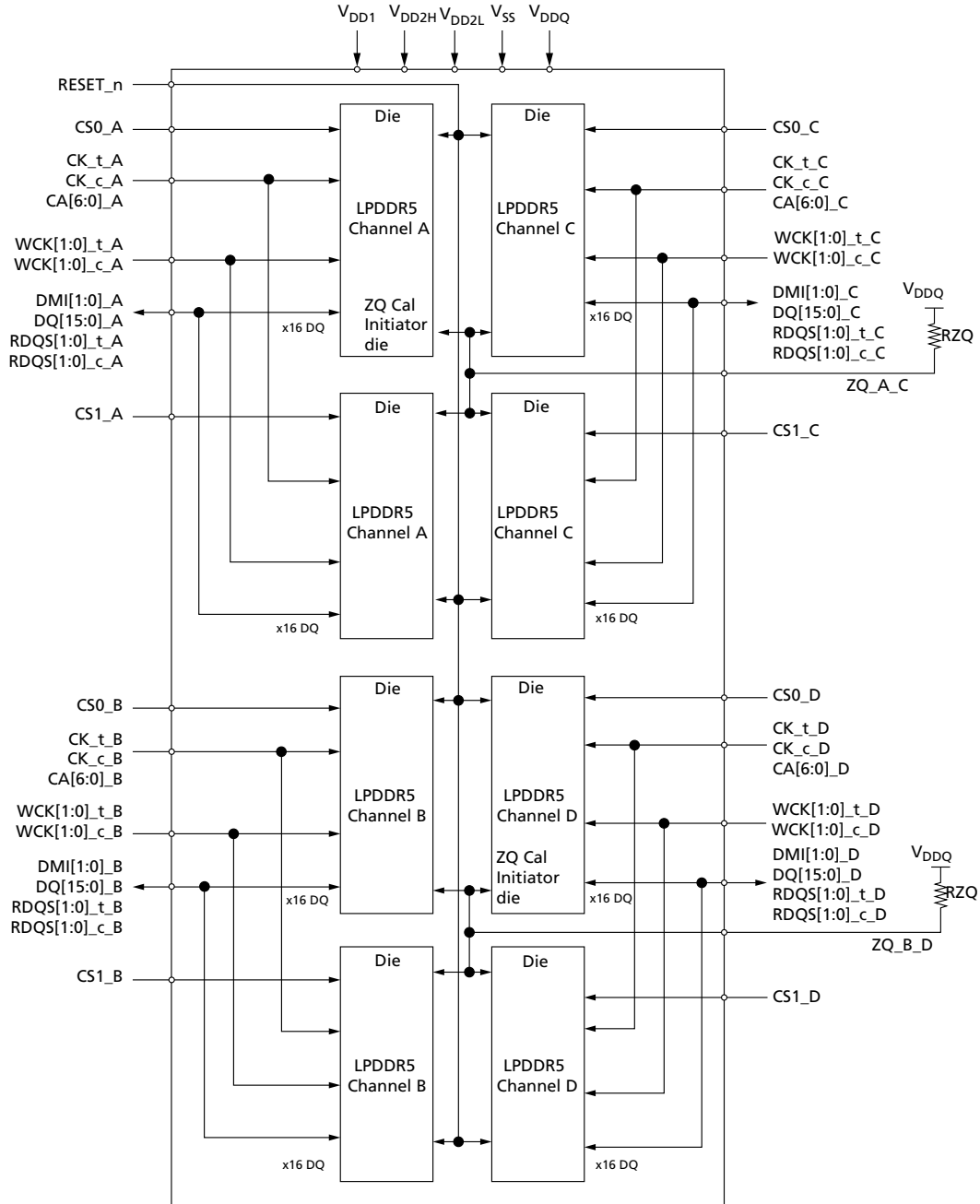
Quad Die, Quad Channel, Single Rank

Figure 6: Quad-Die, Quad-Channel, Single-Rank Package Block Diagram



Eight Die, Quad Channel, Dual Rank

Figure 7: Eight-Die, Quad-Channel, Dual-Rank Package Block Diagram



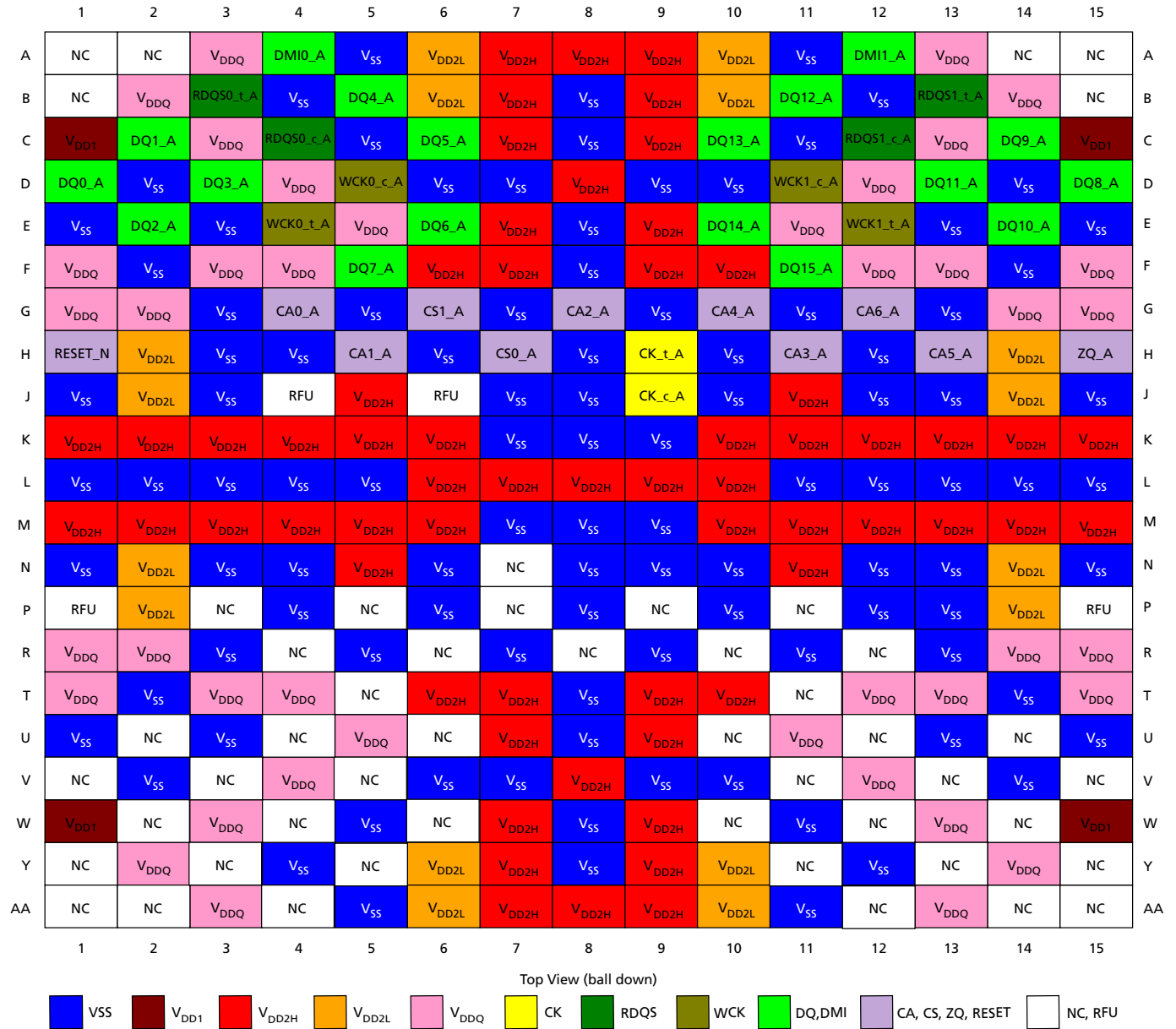
Ball Assignments and Descriptions

315b Single Die, Single Channel, 1 Rank

Table 7: Single Channel 315-Ball/Pad Descriptions

Symbol	Type	Description
CK_t_[A], CK_c_[A]	Input	Clock: CK_t and CK_c are differential clock inputs. All double data rate (DDR) command/address inputs are sampled on both crossing points of CK_t and CK_c. The first crossing point is the rising (falling) edge of CK_t (CK_c) and second crossing point is falling (rising) edge of CK_t (CK_c). Single data rate (SDR) inputs, CS is sampled on the crossing point that is the rising (falling) edge of CK_t (CK_c).
CS0_[A], CS1_[A]	Input	Chip select: CS is part of the command code, and is sampled on the rising (falling) edge of CK_t (CK_c) unless the device is in power-down or deep sleep mode where it becomes an asynchronous signal. Each rank (0, 1) has its own CS signals. CS1_[A:B] become NC pins in a single-rank package.
CA[6:0]_[A]	Input	Command/address inputs: Provide the command and address inputs according to the command truth table.
WCK[1:0]_t_[A], WCK[1:0]_c_[A]	Input	Data clock: WCK_t and WCK_c are differential clock inputs used for write data capture and read data output.
DQ[15:0]_[A]	I/O	Data input/output: Bidirectional data bus.
RDQS[1:0]_t_[A], RDQS[1:0]_c_[A]	I/O Output	Read data strobe: RDQS_t and RDQS_c are differential output clock signals used to strobe data during a READ operation. RDQS_t is also used as a parity pin during write link protection enabled. Each byte of data has RDQS_t and RDQS_c signals.
DMI[1:0]_[A]	I/O	Data mask inversion: DMI serves multiple functions such as data mask (DM), data bus inversion (DBI), and parity at READ with ECC operation by setting the mode register. DMI is a bidirectional signal and each byte of data has a DMI signal.
ZQ_A	Reference	ZQ calibration reference: Used to calibrate the output drive strength and the termination resistance. The ZQ pin should be connected to V _{DDQ} through a 240Ω ±1% resistor.
V _{DDQ} , V _{DD1} , V _{DD2H} , V _{DD2L}	Supply	Power supplies: Isolated on the die for improved noise immunity.
V _{SS}	Supply	Ground reference: Power supply ground reference.
RESET_n	Input	Reset: When asserted LOW, the RESET pin resets the die. Reset is an asynchronous signal.
NC	–	No connect: Not internally connected.
RFU	–	Reserved Future Use: Not internally connected

Figure 8: 315-Ball Single-Channel Discrete FBGA



315b Dual Channel, 1 Rank, 2 Rank

Table 8: 315-Ball/Pad Descriptions

Symbol	Type	Description
CK_t_[A:B], CK_c_[A:B]	Input	Clock: CK_t and CK_c are differential clock inputs. All double data rate (DDR) command/address inputs are sampled on both crossing points of CK_t and CK_c. The first crossing point is the rising (falling) edge of CK_t (CK_c) and second crossing point is falling (rising) edge of CK_t (CK_c). Single data rate (SDR) inputs, CS is sampled on the crossing point that is the rising (falling) edge of CK_t (CK_c).
CS0_[A:B], CS1_[A:B]	Input	Chip select: CS is part of the command code, and is sampled on the rising (falling) edge of CK_t (CK_c) unless the device is in power-down or deep sleep mode where it becomes an asynchronous signal. Each rank (0, 1) has its own CS signals. CS1_[A:B] become NC pins in a single-rank package.
CA[6:0]_[A:B]	Input	Command/address inputs: Provide the command and address inputs according to the command truth table.
WCK[1:0]_t_[A:B], WCK[1:0]_c_[A:B]	Input	Data clock: WCK_t and WCK_c are differential clock inputs used for write data capture and read data output.
DQ[15:0]_[A:B]	I/O	Data input/output: Bidirectional data bus.
RDQS[1:0]_t_[A:B], RDQS[1:0]_c_[A:B]	I/O Output	Read data strobe: RDQS_t and RDQS_c are differential output clock signals used to strobe data during a READ operation. RDQS_t is also used as a parity pin during write link protection enabled. Each byte of data has RDQS_t and RDQS_c signals.
DMI[1:0]_[A:B]	I/O	Data mask inversion: DMI serves multiple functions such as data mask (DM), data bus inversion (DBI), and parity at READ with ECC operation by setting the mode register. DMI is a bidirectional signal and each byte of data has a DMI signal.
ZQ_A	Reference	ZQ calibration reference: Used to calibrate the output drive strength and the termination resistance. The ZQ pin should be connected to V _{DDQ} through a 240Ω ±1% resistor.
V _{DDQ} , V _{DD1} , V _{DD2H} , V _{DD2L}	Supply	Power supplies: Isolated on the die for improved noise immunity.
V _{SS}	Supply	Ground reference: Power supply ground reference.
RESET_n	Input	Reset: When asserted LOW, the RESET pin resets the die. Reset is an asynchronous signal.
NC	–	No connect: Not internally connected.
RFU	–	Reserved Future Use: Not internally connected.

Figure 9: 315-Ball Dual-Channel Discrete FBGA

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	
A	NC	NC	V _{DDQ}	DMI0_A	V _{SS}	V _{DD2L}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2L}	V _{SS}	DMI1_A	V _{DDQ}	NC	NC	A
B	NC	V _{DDQ}	RDQS0_t_A	V _{SS}	DQ4_A	V _{DD2L}	V _{DD2H}	V _{SS}	V _{DD2H}	V _{DD2L}	DQ12_A	V _{SS}	RDQS1_t_A	V _{DDQ}	NC	B
C	V _{DD1}	DQ1_A	V _{DDQ}	RDQS0_c_A	V _{SS}	DQ5_A	V _{DD2H}	V _{SS}	V _{DD2H}	DQ13_A	V _{SS}	RDQS1_c_A	V _{DDQ}	DQ9_A	V _{DD1}	C
D	DQ0_A	V _{SS}	DQ3_A	V _{DDQ}	WCK0_c_A	V _{SS}	V _{SS}	V _{DD2H}	V _{SS}	V _{SS}	WCK1_c_A	V _{DDQ}	DQ11_A	V _{SS}	DQ8_A	D
E	V _{SS}	DQ2_A	V _{SS}	WCK0_t_A	V _{DDQ}	DQ6_A	V _{DD2H}	V _{SS}	V _{DD2H}	DQ14_A	V _{DDQ}	WCK1_t_A	V _{SS}	DQ10_A	V _{SS}	E
F	V _{DDQ}	V _{SS}	V _{DDQ}	V _{DDQ}	DQ7_A	V _{DD2H}	V _{DD2H}	V _{SS}	V _{DD2H}	V _{DD2H}	DQ15_A	V _{DDQ}	V _{DDQ}	V _{SS}	V _{DDQ}	F
G	V _{DDQ}	V _{DDQ}	V _{SS}	CA0_A	V _{SS}	CS1_A	V _{SS}	CA2_A	V _{SS}	CA4_A	V _{SS}	CA6_A	V _{SS}	V _{DDQ}	V _{DDQ}	G
H	RESET_N	V _{DD2L}	V _{SS}	V _{SS}	CA1_A	V _{SS}	CS0_A	V _{SS}	CK_t_A	V _{SS}	CA3_A	V _{SS}	CA5_A	V _{DD2L}	ZQ_A	H
J	V _{SS}	V _{DD2L}	V _{SS}	RFU	V _{DD2H}	RFU	V _{SS}	V _{SS}	CK_c_A	V _{SS}	V _{DD2H}	V _{SS}	V _{SS}	V _{DD2L}	V _{SS}	J
K	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{SS}	V _{SS}	V _{SS}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	K
L	V _{SS}	V _{SS}	V _{SS}	V _{SS}	V _{SS}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{SS}	V _{SS}	V _{SS}	V _{SS}	V _{SS}	L
M	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{SS}	V _{SS}	V _{SS}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	M
N	V _{SS}	V _{DD2L}	V _{SS}	V _{SS}	V _{DD2H}	V _{SS}	CK_c_B	V _{SS}	V _{SS}	V _{SS}	V _{DD2H}	V _{SS}	V _{SS}	V _{DD2L}	V _{SS}	N
P	RFU	V _{DD2L}	CA5_B	V _{SS}	CA3_B	V _{SS}	CK_t_B	V _{SS}	CS0_B	V _{SS}	CA1_B	V _{SS}	V _{SS}	V _{DD2L}	RFU	P
R	V _{DDQ}	V _{DDQ}	V _{SS}	CA6_B	V _{SS}	CA4_B	V _{SS}	CA2_B	V _{SS}	CS1_B	V _{SS}	CA0_B	V _{SS}	V _{DDQ}	V _{DDQ}	R
T	V _{DDQ}	V _{SS}	V _{DDQ}	V _{DDQ}	DQ15_B	V _{DD2H}	V _{DD2H}	V _{SS}	V _{DD2H}	V _{DD2H}	DQ7_B	V _{DDQ}	V _{DDQ}	V _{SS}	V _{DDQ}	T
U	V _{SS}	DQ10_B	V _{SS}	WCK1_t_B	V _{DDQ}	DQ14_B	V _{DD2H}	V _{SS}	V _{DD2H}	DQ6_B	V _{DDQ}	WCK0_t_B	V _{SS}	DQ2_B	V _{SS}	U
V	DQ8_B	V _{SS}	DQ11_B	V _{DDQ}	WCK1_c_B	V _{SS}	V _{SS}	V _{DD2H}	V _{SS}	V _{SS}	WCK0_c_B	V _{DDQ}	DQ3_B	V _{SS}	DQ0_B	V
W	V _{DD1}	DQ9_B	V _{DDQ}	RDQS1_c_B	V _{SS}	DQ13_B	V _{DD2H}	V _{SS}	V _{DD2H}	DQ5_B	V _{SS}	RDQS0_c_B	V _{DDQ}	DQ1_B	V _{DD1}	W
Y	NC	V _{DDQ}	RDQS1_t_B	V _{SS}	DQ12_B	V _{DD2L}	V _{DD2H}	V _{SS}	V _{DD2H}	V _{DD2L}	DQ4_B	V _{SS}	RDQS0_t_B	V _{DDQ}	NC	Y
AA	NC	NC	V _{DDQ}	DMI1_B	V _{SS}	V _{DD2L}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2L}	V _{SS}	DMI0_B	V _{DDQ}	NC	NC	AA

Top View (ball down)

 V _{SS}	 V _{DD1}	 V _{DD2H}	 V _{DD2L}	 V _{DDQ}	 CK	 RDQS	 WCK	 DQ,DMI	 CA, CS, ZQ, RESET	 NC, RFU
--	--	---	--	---	---	--	---	---	---	---



441b Quad Channel, 1 Rank, 2 Rank

Table 9: 441-Ball/Pad Descriptions

Symbol	Type	Description
CK_t_[A:D], CK_c_[A:D]	Input	Clock: CK_t and CK_c are differential clock inputs. All double data rate (DDR) command/address inputs are sampled on both crossing points of CK_t and CK_c. The first crossing point is the rising (falling) edge of CK_t (CK_c) and second crossing point is falling (rising) edge of CK_t (CK_c). Single data rate (SDR) inputs, CS is sampled on the crossing point that is the rising (falling) edge of CK_t (CK_c).
CS0_[A:D], CS1_[A:D]	Input	Chip select: CS is part of the command code, and is sampled on the rising (falling) edge of CK_t (CK_c) unless the device is in power-down or deep sleep mode where it becomes an asynchronous signal. Each rank (0, 1) has its own CS signals. CS1_[A:D] become NC pins in a single-rank package.
CA[6:0]_[A:D]	Input	Command/address inputs: Provide the command and address inputs according to the command truth table.
WCK[1:0]_t_[A:D], WCK[1:0]_c_[A:D]	Input	Data clock: WCK_t and WCK_c are differential clock inputs used for WRITE data capture and READ data output.
DQ[15:0]_[A:D]	I/O	Data input/output: Bidirectional data bus.
RDQS[1:0]_t_[A:D], RDQS[1:0]_c_[A:D]	I/O Output	Read data strobe: RDQS_t and RDQS_c are differential output clock signals used to strobe data during a READ operation. RDQS_t is also used as a parity pin during write link protection enabled. Each byte of data has RDQS_t and RDQS_c signals.
DMI[1:0]_[A:D]	I/O	Data mask inversion: DMI serves multiple functions such as data mask (DM), data bus inversion (DBI), and parity at READ with ECC operation by setting the mode register. DMI is a bidirectional signal and each byte of data has a DMI signal.
ZQ_A_C, ZQ_B_D	Reference	ZQ calibration reference: Used to calibrate the output drive strength and the termination resistance. The ZQ pin should be connected to V _{DDQ} through a 240Ω ±1% resistor.
V _{DDQ} , V _{DD1} , V _{DD2H} , V _{DD2L}	Supply	Power supplies: Isolated on the die for improved noise immunity.
V _{SS}	Supply	Ground reference: Power supply ground reference.
RESET_n	Input	Reset: When asserted LOW, the RESET pin resets the die. Reset is an asynchronous signal.
NC	–	No connect: Not internally connected.
RFU	–	Reserved Future Use: Not internally connected



Y42M LPDDR5X SDRAM
Ball Assignments and Descriptions

Figure 10: 441-Ball Quad-Channel FBGA

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	
A	V _{SS}	V _{SS}	V _{DD1}	V _{DD2L}	V _{SS}	V _{DD2H}	V _{DD1}	V _{SS}	V _{DD2L}	V _{DD2H}	V _{DD2H}	V _{SS}	V _{DD1}	V _{DD2L}	V _{SS}	V _{DD2H}	V _{DD1}	V _{SS}	V _{DD2L}	V _{SS}	V _{SS}	A
B	V _{SS}	DQ0_A	V _{SS}	DQ3_A	V _{DD2H}	V _{SS}	DQ11_A	DQ9_A	DQ8_A	V _{SS}	V _{DD2H}	DQ0_C	V _{SS}	DQ3_C	V _{DD2H}	V _{SS}	DQ11_C	DQ9_C	DQ8_C	RFU	V _{SS}	B
C	V _{DD2H}	V _{SS}	DQ2_A	V _{DDQ}	CA0_A	V _{DD2H}	V _{SS}	DQ10_A	V _{DDQ}	V _{DD2H}	V _{SS}	V _{SS}	DQ2_C	V _{DDQ}	CA0_C	V _{DD2H}	V _{SS}	DQ10_C	V _{DDQ}	V _{DD2H}	V _{DD2H}	C
D	V _{SS}	DQ1_A	WCK0_c_A	V _{SS}	CA1_A	CS0_A	V _{DDQ}	V _{SS}	WCK1_t_A	V _{DD2H}	V _{DDQ}	DQ1_C	WCK0_c_C	V _{SS}	CA1_C	CS0_C	V _{DDQ}	V _{SS}	WCK1_t_C	V _{DDQ}	V _{SS}	D
E	V _{DDQ}	RDQ50_c_A	V _{SS}	WCK0_t_A	V _{SS}	CS1_A	V _{SS}	WCK1_c_A	DMI1_A	V _{SS}	V _{DDQ}	RDQ50_c_C	V _{SS}	WCK0_t_C	V _{SS}	CS1_C	V _{SS}	WCK1_c_C	DMI1_C	V _{SS}	V _{DD2H}	E
F	V _{DDQ}	RDQ50_t_A	V _{SS}	V _{DDQ}	V _{SS}	CA2_A	V _{SS}	RDQ51_t_A	V _{SS}	V _{DDQ}	V _{SS}	RDQ50_t_C	V _{SS}	V _{DDQ}	V _{SS}	CA2_C	V _{SS}	RDQ51_t_C	V _{SS}	V _{DDQ}	V _{DD2H}	F
G	V _{SS}	DQ4_A	V _{DDQ}	DMI0_A	RFU	RFU	CA6_A	V _{SS}	RDQ51_c_A	V _{SS}	V _{DDQ}	DMI0_C	V _{DDQ}	DQ4_C	RFU	RFU	CA6_C	V _{SS}	RDQ51_c_C	V _{SS}	V _{SS}	G
H	V _{DD2L}	V _{SS}	DQ5_A	V _{SS}	CK_t_A	V _{SS}	CA5_A	V _{DDQ}	V _{SS}	DQ12_A	V _{SS}	V _{SS}	DQ5_C	V _{SS}	CK_t_C	V _{SS}	CA5_C	V _{DDQ}	V _{SS}	DQ12_C	V _{DD2L}	H
J	V _{DD2H}	DQ6_A	DQ7_A	V _{DD2H}	V _{SS}	CK_c_A	V _{SS}	DQ14_A	DQ13_A	V _{SS}	V _{DD2L}	DQ6_C	DQ7_C	V _{DD2L}	ZQ_A_C	CK_c_C	V _{SS}	DQ14_C	DQ13_C	V _{SS}	V _{DD2H}	J
K	V _{SS}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{SS}	CA3_A	CA4_A	V _{DD2L}	V _{SS}	DQ15_A	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{SS}	CA3_C	CA4_C	V _{DD2H}	V _{SS}	DQ15_C	V _{SS}	K
L	V _{DD2H}	V _{DD2L}	V _{DD2L}	V _{DD2H}	V _{DD2L}	V _{DD2H}	V _{SS}	V _{DD2H}	V _{DD2H}	V _{SS}	V _{SS}	V _{SS}	V _{DD2H}	V _{DD2H}	V _{SS}	V _{DD2H}	V _{DD2L}	V _{DD2H}	V _{DD2L}	V _{DD2L}	V _{DD2H}	L
M	V _{SS}	DQ15_B	V _{SS}	V _{DD2H}	CA4_B	CA3_B	V _{SS}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{DD2H}	DQ15_D	V _{SS}	V _{DD2L}	CA4_D	CA3_D	V _{SS}	V _{DD2H}	V _{DD2H}	V _{DD2H}	V _{SS}	M
N	V _{DD2H}	V _{SS}	DQ13_B	DQ14_B	V _{SS}	CK_c_B	ZQ_B_D	V _{DD2L}	DQ7_B	DQ6_B	V _{DD2L}	V _{SS}	DQ13_D	DQ14_D	V _{SS}	CK_c_D	V _{SS}	V _{DD2H}	DQ7_D	DQ6_D	V _{DD2H}	N
P	V _{DD2L}	DQ12_B	V _{SS}	V _{DDQ}	CA5_B	V _{SS}	CK_t_B	V _{SS}	DQ5_B	V _{SS}	V _{SS}	DQ12_D	V _{SS}	V _{DDQ}	CA5_D	V _{SS}	CK_t_D	V _{SS}	DQ5_D	V _{SS}	V _{DD2L}	P
R	V _{SS}	V _{SS}	RDQ51_c_B	V _{SS}	CA6_B	RFU	RFU	DQ4_B	V _{DDQ}	DMI0_B	V _{DDQ}	V _{SS}	RDQ51_c_D	V _{SS}	CA6_D	RFU	RFU	DMI0_D	V _{DDQ}	DQ4_D	V _{SS}	R
T	V _{DD2H}	V _{DDQ}	V _{SS}	RDQ51_t_B	V _{SS}	CA2_B	V _{SS}	V _{DDQ}	V _{SS}	RDQ50_t_B	V _{SS}	V _{DDQ}	V _{SS}	RDQ51_t_D	V _{SS}	CA2_D	V _{SS}	V _{DDQ}	V _{SS}	RDQ50_t_D	V _{DDQ}	T
U	V _{DD2H}	V _{SS}	DMI1_B	WCK1_c_B	V _{SS}	CS1_B	V _{SS}	WCK0_t_B	V _{SS}	RDQ50_c_B	V _{DDQ}	V _{SS}	DMI1_D	WCK1_c_D	V _{SS}	CS1_D	V _{SS}	WCK0_t_D	V _{SS}	RDQ50_c_D	V _{DDQ}	U
V	V _{SS}	V _{DDQ}	WCK1_t_B	V _{SS}	V _{DDQ}	CS0_B	CA1_B	V _{SS}	WCK0_c_B	DQ1_B	V _{DDQ}	V _{DD2H}	WCK1_t_D	V _{SS}	V _{DDQ}	CS0_D	CA1_D	V _{SS}	WCK0_c_D	DQ1_D	V _{SS}	V
W	V _{DD2H}	V _{DD2H}	V _{DDQ}	DQ10_B	V _{SS}	V _{DD2H}	CA0_B	V _{DDQ}	DQ2_B	V _{SS}	V _{SS}	V _{DD2H}	V _{DDQ}	DQ10_D	V _{SS}	V _{DD2H}	CA0_D	V _{DDQ}	DQ2_D	V _{SS}	V _{DD2H}	W
Y	V _{SS}	RESET_N	DQ8_B	DQ9_B	DQ11_B	V _{SS}	V _{DD2H}	DQ3_B	V _{SS}	DQ0_B	V _{DD2H}	V _{SS}	DQ8_D	DQ9_D	DQ11_D	V _{SS}	V _{DD2H}	DQ3_D	V _{SS}	DQ0_D	V _{SS}	Y
AA	V _{SS}	V _{SS}	V _{DD2L}	V _{SS}	V _{DD1}	V _{DD2H}	V _{SS}	V _{DD2L}	V _{DD1}	V _{SS}	V _{DD2H}	V _{DD2H}	V _{DD2L}	V _{SS}	V _{DD1}	V _{DD2H}	V _{SS}	V _{DD2L}	V _{DD1}	V _{SS}	V _{SS}	AA

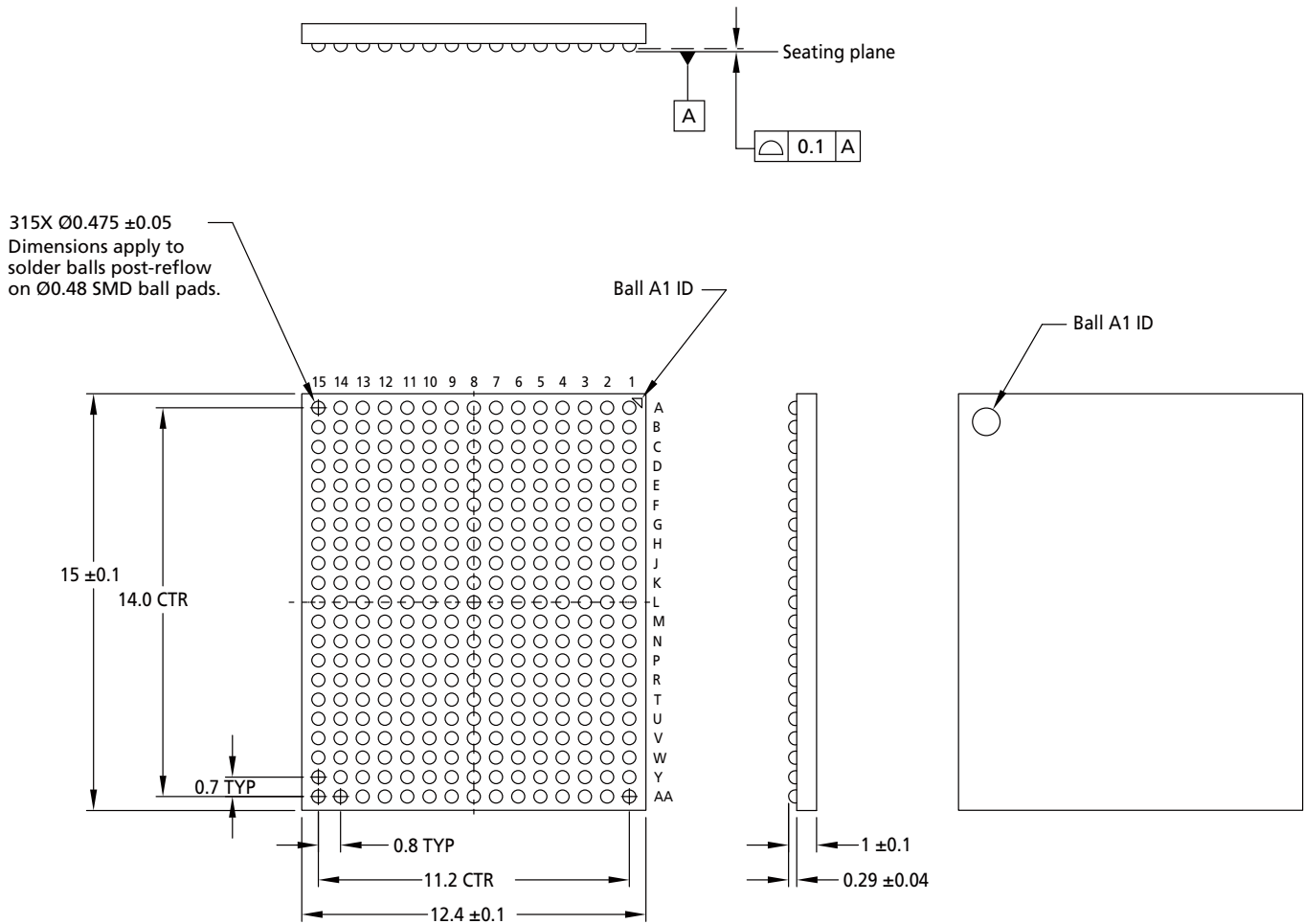
Top View (ball down)



Package Dimensions

315-Ball Package (Package Code: DS)

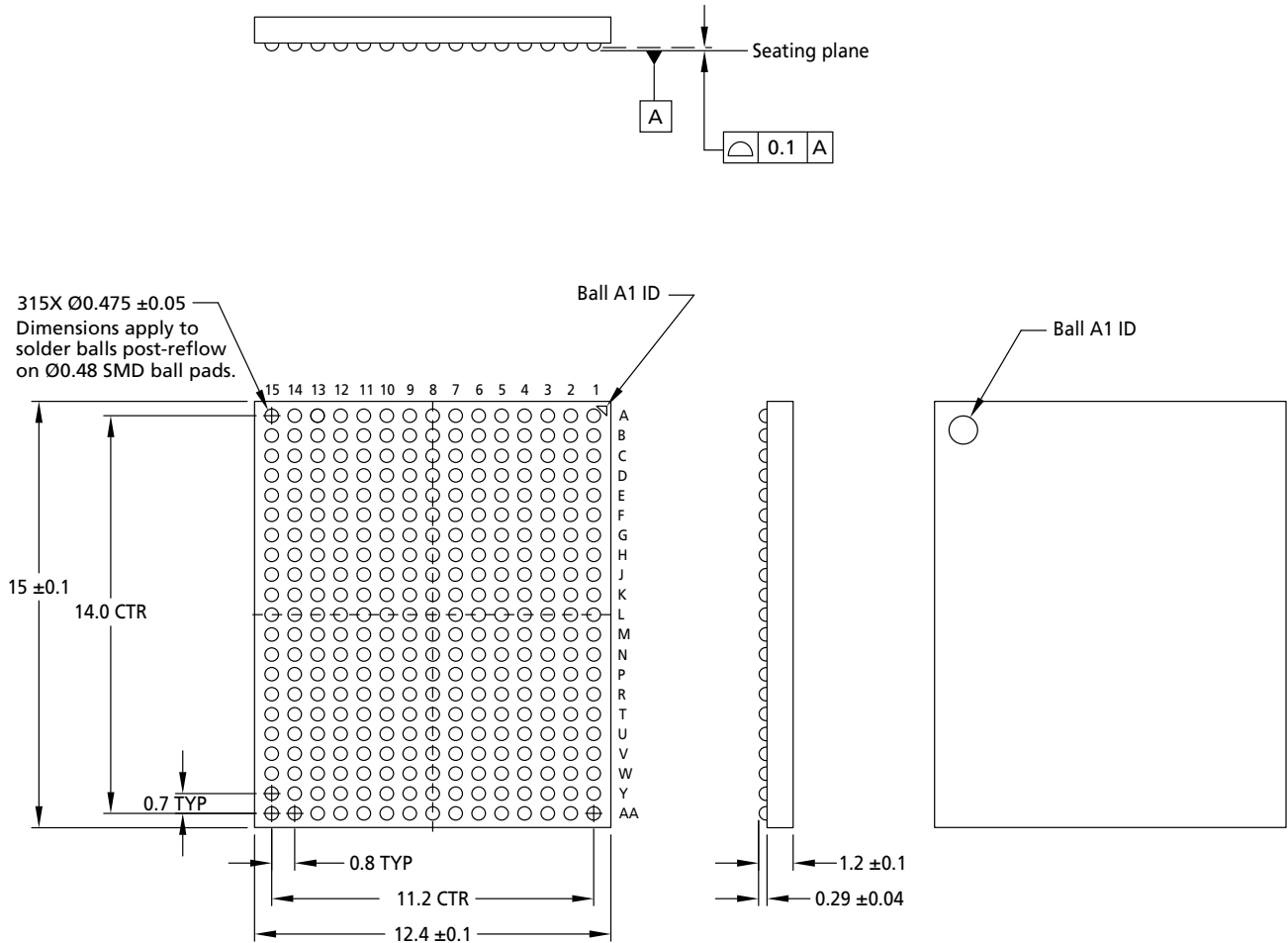
Figure 11: 315-Ball TFBGA – 12.4mm (TYP) × 15.0mm (TYP) × 1.1mm (MAX) (Package Code: DS)



- Notes: 1. All dimensions are in millimeters.
2. Solder ball composition: SACQ with CuOSP pads (Sn-4Ag-0.5Cu-3Bi-0.05Ni)

315-Ball Package (Package Code: DV)

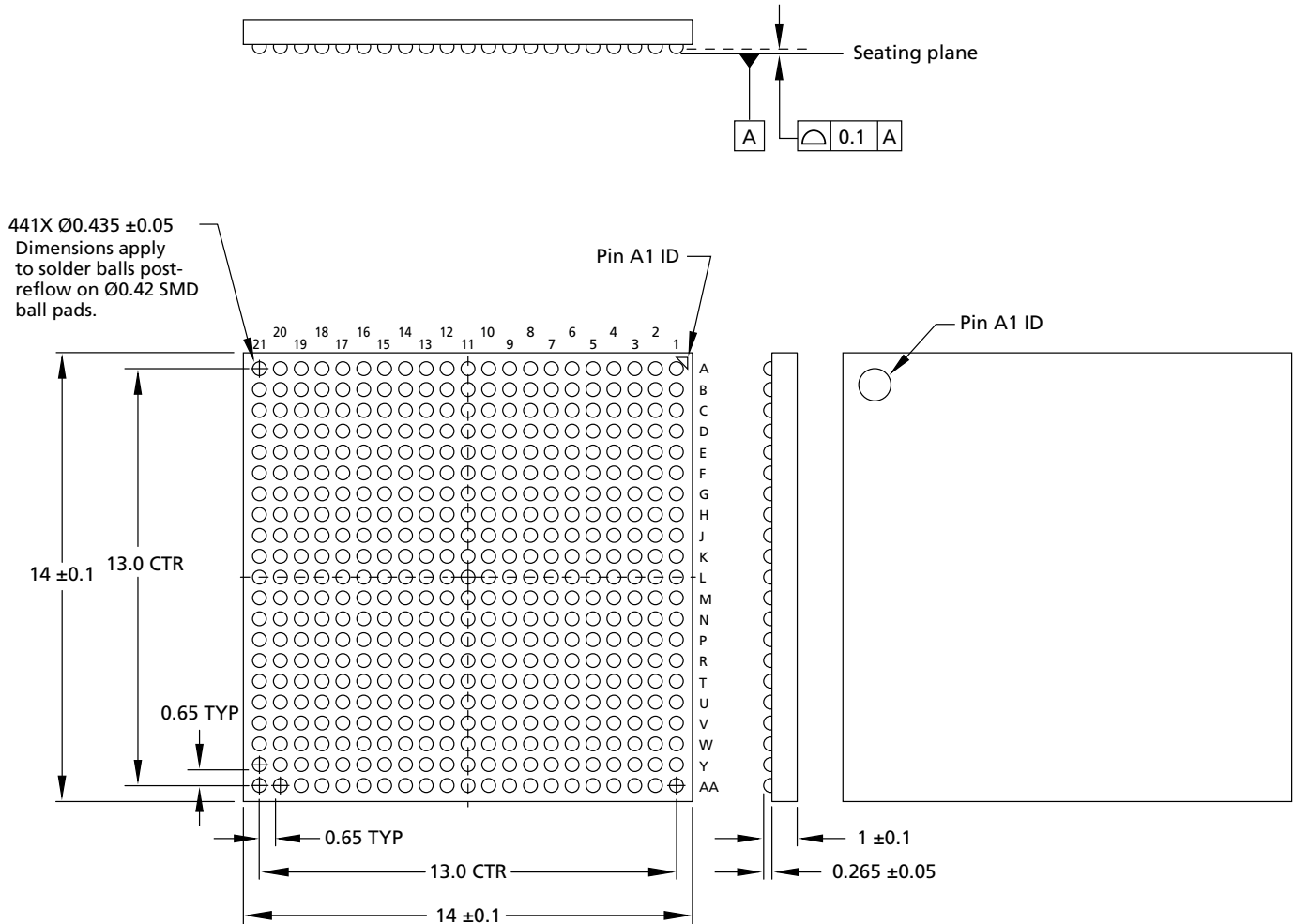
Figure 12: 315-Ball LFBGA – 12.4mm (TYP) × 15.0mm (TYP) × 1.3mm (MAX) (Package Code: DV)



- Notes: 1. All dimensions are in millimeters.
 2. Solder ball composition: SACQ with CuOSP pads (Sn-4Ag-0.5Cu-3Bi-0.05Ni)

441-Ball Package (Package Code: EK)

Figure 13: 441-Ball TFBGA – 14.0mm (TYP) × 14.0mm (TYP) × 1.1mm (MAX) (Package Code: EK)



- Notes: 1. All dimensions are in millimeters.
 2. Solder ball composition: SACQ with CuOSP pads (Sn- 4Ag-0.5Cu-3Bi-0.05Ni)



Product-Specific Mode Register Definition

Table 10: Mode Register Contents

Mode Register	OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0	
MR0	Per-pin DFE	Pre Emphasis	Unified NT ODT behavior mode	DMI output behavior mode	Optimized refresh mode	Enhanced WCK always-on mode	Latency mode	NT ODT timing mode	
	OP[0] = 1b: Device supports different NT ODT latency for DQ and RDQS								
	OP[1] = 0b: Device supports x16 mode latency for 1G16, 1G32, 2G32, 1G64, 2G64 OP[1] = 1b: Device supports x8 mode latency for 4G32								
	OP[2] = 1b: Device supports enhanced WCK always-on mode								
	OP[3] = 1b: Device supports optimized refresh mode								
	OP[4] = 1b: Device supports both DMI behavior mode 1 and 2 and mode selection								
	OP[5] = 1b: The NT ODT behavior follows the unified NT ODT behavior								
	OP[6] = 1b: Device supports Pre Emphasis mode								
	OP[7] = 0b: Device does not support Per Pin DFE								
MR1							ARFM support ³	CS ODT OP support	
	OP[0] = 1b: Device supports CS ODT behavior OP OP[1] = 1b: Device supports ARFM								
MR3				BK/BG Org					
	OP[4:3] = 00b: BG, 01b: 8B, 10b: 16B Mode Supported								
MR5	Manufacturer ID								
	1111 1111b: Micron								
MR6	Revision ID1								
	0000 0111b								
MR8	I/O width		Density			Type			
	OP[7:6] = 00b: x16 for 1G16, 1G32, 2G32, 1G64, 2G64 OP[7:6] = 01b: x8 for 4G32		OP[5:2] = 0110b: 16Gb			OP[1:0] = 01b: LPDDR5X SDRAM			
MR13						VRO			
	OP[2] = 0b: Normal operation (default) 1b: Output the $V_{REF(CA)}$ value on DQ7 and $V_{REF(DQ)}$ value on DQ6								
MR19			WCK2DQ OSC FM						
	OP[5] = 1b: WCK2DQ OSC FM supported								

Table 10: Mode Register Contents (Continued)

Mode Register	OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
MR21	WXS				ODTD-CSFS	WXFS	RDCFS	WDCFS
	OP[0] = 1b: WRITE DATA COPY function supported							
	OP[1] = 1b: READ DATA COPY function supported							
	OP[2] = 1b: WRITE X function supported							
	OP[3] = 1b: Device ODTD-CS is supported							
	OP[7] = 1b: Data to be written can be selected with 0 and 1							
MR22	RECC		WECC					
	OP[5:4] = 00b: Write link ECC disabled (default) 01b: Write link ECC enabled (See Note 4)							
	OP[7:6] = 00b: Read link ECC disabled (default) 01b: Read link ECC enabled (See Note 4)							
MR24	DFES				Read DCA			
	OP[3] = 1b: Device supports Read DCA							
	OP[7] = 1b: Device supports DFE (See Note 5)							
MR26		RDQSTFS						
	OP[6] = 1b: Read/write-based RDQS_t TRAINING function supported							
MR27	RAAMULT		RAAIMT				RFM	
	OP[0] = 1b: RFM is required							
	OP[5:1] = 01110b: 112							
	OP[7:6] = 01b: 4X							
MR41						DVFSC/ E-DVFSC Support		
	OP[2:1] = 00b: Only Legacy DVFSC Mode supported							
MR43		SBEC rule						
	OP[6] = 1b: Simultaneous SBE on each DQ byte and DMI are independently counted							
MR57	ARFM³				RFMSB		RAADEC	
	OP[1:0] = 10b: 2 × RAAIMT							
	OP[3:2] = 00b: 1 = Does not support single-bank mode							
	OP[7:6] = 00b: default (01110b: 112), 01b: Level A = 01101b: 104, Level B = 01100b: 96, Level C = 01011: 88							
MR63 - MR164	Reserved MR bits MR63 through MR164 are RFU by JEDEC standard and should not be accessed by user unless directed by supplier.							

- Notes: 1. The contents of mode registers described here reflect information specific to each die in these packages.
2. Refer to General LPDDR5/LPDDR5X Specification 1 for mode registers not described here.
3. Refer to General LPDDR5/LPDDR5X Specification 3 for feature description not described here.
4. Write link ECC and read link ECC are supported.
5. Device supports 3-step DFE.



I_{DD} Parameters

Refer to I_{DD} Specification Parameters and Test Conditions section in General LPDDR5/LPDDR5X Specifications 2 for detailed conditions.

Table 11: WT I_{DD} Parameters – Single Die

Symbol	Supply	Speed Grade				Unit	Note
		x8 Mode		x16 Mode			
		7500 Mb/s	8533 Mb/s	7500 Mb/s	8533 Mb/s		
I _{DD01}	V _{DD1}	3.20	3.20	3.20	3.20	mA	
I _{DD02H}	V _{DD2H}	28.50	28.50	29.00	29.00		
I _{DD02L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD0Q}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD2P1}	V _{DD1}	1.50	1.50	1.50	1.50	mA	
I _{DD2P2H}	V _{DD2H}	2.50	2.50	2.50	2.50		
I _{DD2P2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD2PQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD2PS1}	V _{DD1}	1.50	1.50	1.50	1.50	mA	
I _{DD2PS2H}	V _{DD2H}	2.50	2.50	2.50	2.50		
I _{DD2PS2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD2PSQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD2N1}	V _{DD1}	1.50	1.50	1.50	1.50	mA	
I _{DD2N2H}	V _{DD2H}	16.50	16.50	17.00	17.00		
I _{DD2N2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD2NQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD2NS1}	V _{DD1}	1.50	1.50	1.50	1.50	mA	
I _{DD2NS2H}	V _{DD2H}	16.50	16.50	17.00	17.00		
I _{DD2NS2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD2NSQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD3P1}	V _{DD1}	1.50	1.50	1.50	1.50	mA	
I _{DD3P2H}	V _{DD2H}	6.50	6.50	6.50	6.50		
I _{DD3P2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD3PQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD3PS1}	V _{DD1}	1.50	1.50	1.50	1.50	mA	
I _{DD3PS2H}	V _{DD2H}	6.50	6.50	6.50	6.50		
I _{DD3PS2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD3PSQ}	V _{DDQ}	0.60	0.60	0.60	0.60		



Table 11: WT I_{DD} Parameters – Single Die

Symbol	Supply	Speed Grade				Unit	Note
		x8 Mode		x16 Mode			
		7500 Mb/s	8533 Mb/s	7500 Mb/s	8533 Mb/s		
I _{DD3N1}	V _{DD1}	1.80	1.80	1.80	1.80	mA	
I _{DD3N2H}	V _{DD2H}	20.50	20.50	21.00	21.00		
I _{DD3N2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD3NQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD3NS1}	V _{DD1}	1.80	1.80	1.80	1.80	mA	
I _{DD3NS2H}	V _{DD2H}	20.50	20.50	21.00	21.00		
I _{DD3NS2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD3NSQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD4R1}	V _{DD1}	9.00	9.00	11.00	12.00	mA	3, 4
I _{DD4R2H}	V _{DD2H}	295.00	325.00	435.00	485.00		
I _{DD4R2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD4RQ}	V _{DDQ}	58.00	63.00	116.00	126.00		
I _{DD4W1}	V _{DD1}	8.00	9.00	10.00	11.00	mA	3
I _{DD4W2H}	V _{DD2H}	225.00	245.00	305.00	335.00		
I _{DD4W2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD4WQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD51}	V _{DD1}	23.00	23.00	23.00	23.00	mA	
I _{DD52H}	V _{DD2H}	165.00	165.00	165.00	165.00		
I _{DD52L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD5Q}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD5AB1}	V _{DD1}	3.20	3.20	3.20	3.20	mA	
I _{DD5AB2H}	V _{DD2H}	26.50	26.50	27.00	27.00		
I _{DD5AB2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD5ABQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD5PB1}	V _{DD1}	3.20	3.20	3.20	3.20	mA	
I _{DD5PB2H}	V _{DD2H}	26.50	26.50	27.00	27.00		
I _{DD5PB2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD5PBQ}	V _{DDQ}	0.60	0.60	0.60	0.60		

- Notes: 1. Applies to entire table: Published I_{DD} values except I_{DD4RQ} are the maximum I_{DD} values considering the worst-case conditions of process, temperature, and voltage.
 2. Applies to entire table: BG mode. DVFS and DVFSQ disabled.
 3. BL = 16, DBI disabled.
 4. I_{DD4RQ} value is reference only. Typical value. Output load = 5pF; R_{ON} = 40 ohms; T_C = 25°C
 5. V_{DD1} = 1.70–1.95V; V_{DD2H} = 1.01–1.12V; V_{DD2L} = 0.87–0.97V; V_{DDQ} = 0.47–0.57V; T_C = –25°C to +85°C

Table 12: WT Full-Array Power-Down Self Refresh Current – Single Die

Temperature	Symbol	Supply	Value	Unit
25°C	I _{DD61}	V _{DD1}	0.27	mA
	I _{DD62H}	V _{DD2H}	0.60	
	I _{DD62L}	V _{DD2L}	(See note 4)	
	I _{DD6Q}	V _{DDQ}	(See note 4)	
85°C	I _{DD61}	V _{DD1}	3.30	
	I _{DD62H}	V _{DD2H}	13.00	
	I _{DD62L}	V _{DD2L}	0.20	
	I _{DD6Q}	V _{DDQ}	0.60	

- Notes: 1. I_{DD6}25°C is the typical value in the distribution with nominal V_{DD} and a reference-only value. I_{DD6}85°C is the maximum I_{DD} guaranteed value considering the worst-case conditions of process, temperature, and voltage.
2. DVFS_C and DVFS_Q disabled.
3. V_{DD1} = 1.70–1.95V; V_{DD2H} = 1.01–1.12V; V_{DD2L} = 0.87–0.97V; V_{DDQ} = 0.47–0.57V; T_C = –25°C to +85°C
4. V_{DD2L} and V_{DDQ} power rails are not used during power-down self refresh.



Table 13: IT I_{DD} Parameters – Single Die

Symbol	Supply	Speed Grade				Unit	Note
		x8 Mode		x16 Mode			
		7500 Mb/s	8533 Mb/s	7500 Mb/s	8533 Mb/s		
I _{DD01}	V _{DD1}	3.30	3.30	3.30	3.30	mA	
I _{DD02H}	V _{DD2H}	30.50	30.50	31.00	31.00		
I _{DD02L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD0Q}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD2P1}	V _{DD1}	1.60	1.60	1.60	1.60	mA	
I _{DD2P2H}	V _{DD2H}	2.70	2.70	2.70	2.70		
I _{DD2P2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD2PQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD2PS1}	V _{DD1}	1.60	1.60	1.60	1.60	mA	
I _{DD2PS2H}	V _{DD2H}	2.70	2.70	2.70	2.70		
I _{DD2PS2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD2PSQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD2N1}	V _{DD1}	1.60	1.60	1.60	1.60	mA	
I _{DD2N2H}	V _{DD2H}	17.50	17.50	18.00	18.00		
I _{DD2N2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD2NQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD2NS1}	V _{DD1}	1.60	1.60	1.60	1.60	mA	
I _{DD2NS2H}	V _{DD2H}	17.50	17.50	18.00	18.00		
I _{DD2NS2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD2NSQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD3P1}	V _{DD1}	1.60	1.60	1.60	1.60	mA	
I _{DD3P2H}	V _{DD2H}	7.00	7.00	7.00	7.00		
I _{DD3P2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD3PQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD3PS1}	V _{DD1}	1.60	1.60	1.60	1.60	mA	
I _{DD3PS2H}	V _{DD2H}	7.00	7.00	7.00	7.00		
I _{DD3PS2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD3PSQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD3N1}	V _{DD1}	1.90	1.90	1.90	1.90	mA	
I _{DD3N2H}	V _{DD2H}	22.50	22.50	23.00	23.00		
I _{DD3N2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD3NQ}	V _{DDQ}	0.60	0.60	0.60	0.60		



Table 13: IT I_{DD} Parameters – Single Die

Symbol	Supply	Speed Grade				Unit	Note
		x8 Mode		x16 Mode			
		7500 Mb/s	8533 Mb/s	7500 Mb/s	8533 Mb/s		
I _{DD3NS1}	V _{DD1}	1.90	1.90	1.90	1.90	mA	
I _{DD3NS2H}	V _{DD2H}	22.50	22.50	23.00	23.00		
I _{DD3NS2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD3NSQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD4R1}	V _{DD1}	9.00	10.00	11.00	12.00	mA	3, 4
I _{DD4R2H}	V _{DD2H}	300.00	330.00	440.00	490.00		
I _{DD4R2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD4RQ}	V _{DDQ}	58.00	63.00	116.00	126.00		
I _{DD4W1}	V _{DD1}	8.00	9.00	10.00	11.00	mA	3
I _{DD4W2H}	V _{DD2H}	230.00	250.00	310.00	340.00		
I _{DD4W2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD4WQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD51}	V _{DD1}	23.00	23.00	23.00	23.00	mA	
I _{DD52H}	V _{DD2H}	165.00	165.00	165.00	165.00		
I _{DD52L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD5Q}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD5AB1}	V _{DD1}	3.20	3.20	3.20	3.20	mA	
I _{DD5AB2H}	V _{DD2H}	26.50	26.50	27.00	27.00		
I _{DD5AB2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD5ABQ}	V _{DDQ}	0.60	0.60	0.60	0.60		
I _{DD5PB1}	V _{DD1}	3.20	3.20	3.20	3.20	mA	
I _{DD5PB2H}	V _{DD2H}	26.50	26.50	27.00	27.00		
I _{DD5PB2L}	V _{DD2L}	0.20	0.20	0.20	0.20		
I _{DD5PBQ}	V _{DDQ}	0.60	0.60	0.60	0.60		

- Notes: 1. Applies to entire table: Published I_{DD} values except I_{DD4RQ} are the maximum I_{DD} values considering the worst-case conditions of process, temperature, and voltage.
 2. Applies to entire table: BG mode. DVFS and DVFSQ disabled.
 3. BL = 16, DBI disabled.
 4. I_{DD4RQ} value is reference only. Typical value. Output load = 5pF; R_{ON} = 40 ohms; T_C = 25°C
 5. V_{DD1} = 1.70–1.95V; V_{DD2H} = 1.01–1.12V; V_{DD2L} = 0.87–0.97V; V_{DDQ} = 0.47–0.57V; T_C = –40°C to +95°C

Table 14: IT Full-Array Power-Down Self Refresh Current – Single Die

Temperature	Symbol	Supply	Value	Unit
25°C	I _{DD61}	V _{DD1}	0.27	mA
	I _{DD62H}	V _{DD2H}	0.60	
	I _{DD62L}	V _{DD2L}	(See note 4)	
	I _{DD6Q}	V _{DDQ}	(See note 4)	
95°C	I _{DD61}	V _{DD1}	3.70	
	I _{DD62H}	V _{DD2H}	16.00	
	I _{DD62L}	V _{DD2L}	0.20	
	I _{DD6Q}	V _{DDQ}	0.60	

- Notes: 1. I_{DD6}25°C is the typical value in the distribution with nominal V_{DD} and a reference-only value. I_{DD6}85°C is the maximum I_{DD} guaranteed value considering the worst-case conditions of process, temperature, and voltage.
2. DVFS and DVFSQ disabled.
3. V_{DD1} = 1.70–1.95V; V_{DD2H} = 1.01–1.12V; V_{DD2L} = 0.87–0.97V; V_{DDQ} = 0.47–0.57V; T_C = –40°C to +95°C